

DZ37062D0L

Silicon epitaxial planar type

For surge absorption circuit

■ Features

- Excellent rising characteristics of zener current I_Z
- Low zener operating resistance R_Z
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 01

■ Packaging

Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Rating	Unit
Total power dissipation ^{*1}	PT	150	mW
Electrostatic discharge ^{*2}	ESD	±10	kV
Junction temperature	T_j	150	$^{\circ}\text{C}$
Operating ambient temperature	T_{opr}	-40 to +85	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

Note) *1: Mounted on glass epoxy print board. (45 mm x 45 mm x 1 mm)

(2 Diode total)

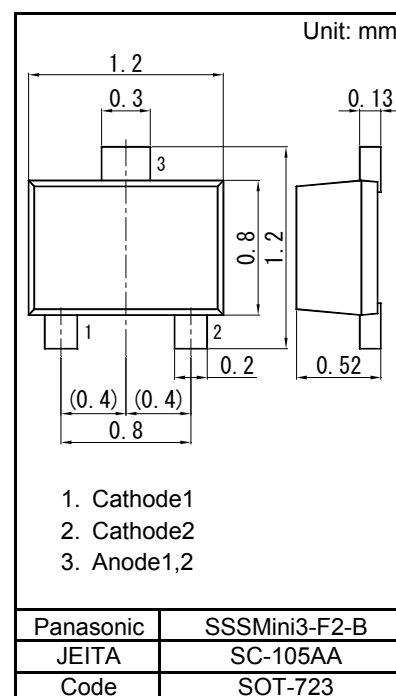
Solder in (Recommended land pattern)

*2: Test method: IEC61000_4_2(C = 150 pF, R = 330 Ω , Contact discharge: 10 times)

■ Electrical Characteristics $T_a = 25\text{ }^{\circ}\text{C} \pm 3\text{ }^{\circ}\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V _F	$I_F = 10\text{ mA}$			1.0	V
Zener voltage ^{*1, *2}	V _Z	$I_Z = 5\text{ mA}$	5.89		6.51	V
Zener operating resistance	R _Z	$I_Z = 5\text{ mA}$			50	Ω
Zener rise operating resistance	R _{ZK}	$I_Z = 0.5\text{ mA}$			100	Ω
Reverse current	I _R	$V_R = 4\text{ V}$			0.2	μA
Temperature coefficient of zener voltage ^{*3}	SZ	$I_Z = 5\text{ mA}$		2.3		mV/ $^{\circ}\text{C}$

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.

2. *1: The temperature must be controlled 25 $^{\circ}\text{C}$ for V_Z measurement.V_Z value measured at other temperature must be adjusted to V_Z (25 $^{\circ}\text{C}$)*2: V_Z guaranteed 20 ms after current flow.*3: $T_j = 25\text{ }^{\circ}\text{C}$ to 150 $^{\circ}\text{C}$ 

Internal Connection

